Sheet 1 of 2

Form PTO-1449 (Rev. 8-83)

U.S. Department of Commerce Patent and Trademark Office

Attorney Docket No. 0756-2218

Serial No. Not Yet Assigned

## INFORMATION DISCLOSURE STATEMENT

Applicant: Hongyong ZHANG et al

Examiner	Evan Pert		Date Considered	5/	21/0/		
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Form PTO-1 (Rev. 8-83			Attorney Docket No.	0756-2218	Serial No. Not	Yet Assigned						
INFO	RMATION DISCLOSURE STAT	EMENT	Applicant: Hongyon	g ZHANG e	t al	P To	·					
	(Use several sheets if necessary)		Filing Date: October	25, 2000	Group: 2813	5954 5954						
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*EXAMINER	: Initial if citation considered, when	ther or not ci		ance with	MDED 600- D	raw lina thra	uah					

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INEO	DMATION I	NICCI		Application Number	09/695,414
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Filing Date	October 25, 2000
				First Named Inventor	Hongyong ZHANG et al.
				Group Art Unit	2829
				Examiner Name	E. Pert
Sheet	1	of	1	Attorney Docket Number	0756-2218

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Examiner Initials*	Cite No.1	U.S. Patent Document		Name of Patentee or Applicant of Cited	Date of Publication of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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	Office <sup>3</sup>	Number <sup>4</sup>	(if known)			0		
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	No.1	No. <sup>1</sup> Office <sup>3</sup> Cite	No.¹ Office³ Number⁴  Office³ Number⁴	No. 1 Office 3 Number 4 (if known)  OTHER PRIOR  Cite Include name of the aut	No. Name of Patentee or Applicant of Cited Document    Name of Patentee or Applicant of Cited Document	No.1  Name of Patentee or Applicant of Cited Document  Name of Patentee or Applicant of Cited Document  Name of Patentee or Applicant of Cited Document  MM-DD-YYYY  OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS  Cite Include name of the author (in CAPITAL LETTERS), title of the article (when approitem (book, magazine, journal, serial, symposium, catalog, etc.)., date, page(s), volum	Name of Patentee or Applicant of Cited Document MM-DD-YYYY    Number	

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